

ABSTRACT OF THE DISCLOSURE

SILICON COMPOUNDS AND METHODS FOR DEPOSITING FILMS USING SAME

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A composition, and chemical vapor deposition method, is provided for producing a dielectric film. A gaseous reagent including the composition is introduced into the reaction chamber in which a substrate is provided. The gaseous reagent includes a silicon precursor that includes a silicon compound according to Formula I as defined herein. Energy is applied to the gaseous reagents in the reaction chamber to induce reaction of the gaseous reagents and to thereby deposit a film on the substrate. The film as deposited is suitable for its intended use without an optional additional cure step applied to the as-deposited film. A method for making the composition is also disclosed.

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15 [No figure]